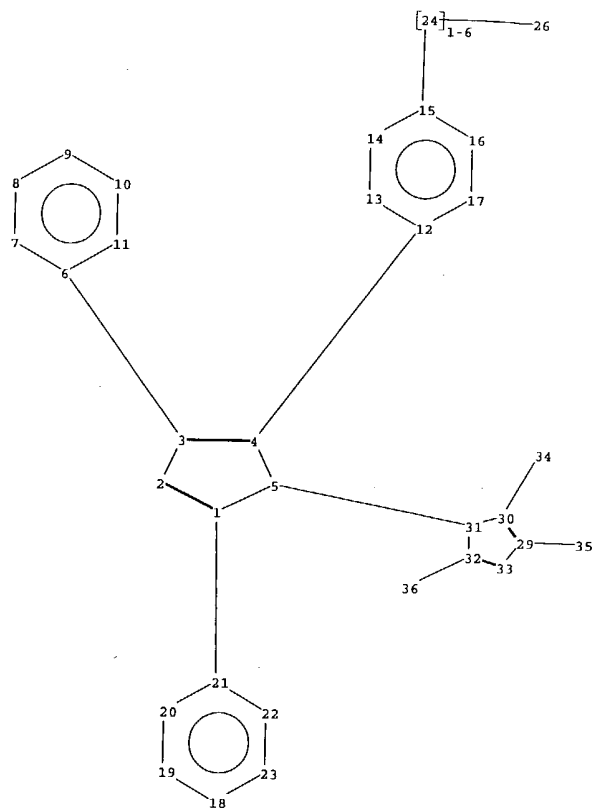
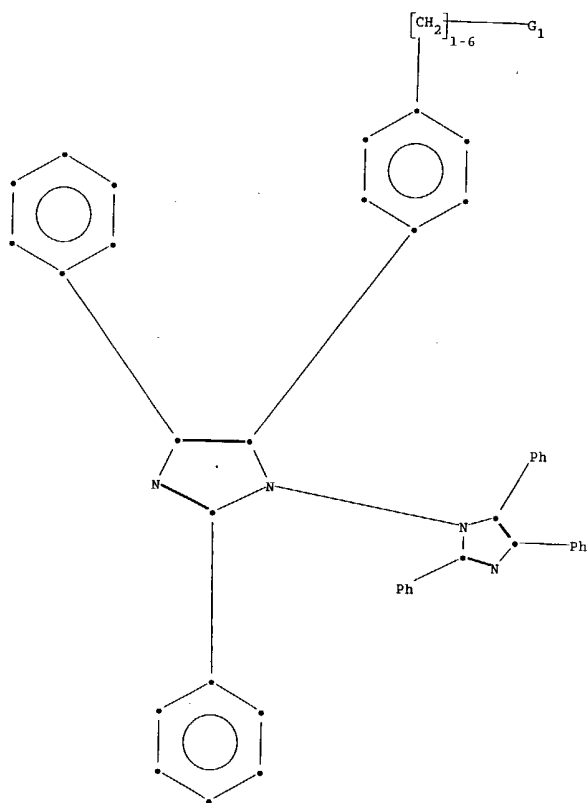


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2	3	photoinitiator near5 (hydrophilic adj carrier)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/14 17:34
4	4	hydrophilic adj photoinitiator	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/14 19:30
3	77	photoinitiator near5 (hydrophilic)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/14 18:02
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6	166	HABI	USPAT	2004/11/14 18:22
7	42	HABI	US-PGPUB	2004/11/14 18:26
8	275	HABI	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/14 18:26
9	141370	PHOTORESIST OR RESIST ADJ COMPOSITION	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/14 18:27
10	102	HABI AND (PHOTORESIST OR RESIST ADJ COMPOSITION)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/14 19:00
11	1811	BARR.IN.	USPAT; US-PGPUB	2004/11/14 19:01
12	609	LUNDY.IN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/14 19:06
13	26	BARR.IN. AND LUNDY.IN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/14 19:06
14	2	6180319.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/14 19:30

C:\Program Files\Stnexp\Queries\697C.str



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chain nodes :
 24 26 34 35 36
ring nodes :
 1 2 3 4 5 6 7 8 9 10 11 12 13 14 15 16 17 18 19 20 21 22 23 29 30
 31 32 33
chain bonds :
 1-21 3-6 4-12 5-31 15-24 24-26 29-35 30-34 32-36
ring bonds :
 1-2 1-5 2-3 3-4 4-5 6-7 6-11 7-8 8-9 9-10 10-11 12-13 12-17 13-14 14-15
 15-16 16-17 18-19 18-23 19-20 20-21 21-22 22-23 29-33 29-30 30-31 31-32 32-33
exact/norm bonds :
 1-2 1-5 2-3 3-4 4-5 5-31 24-26 29-33 29-30 30-31 31-32 32-33
exact bonds :
 1-21 3-6 4-12 15-24 29-35 30-34 32-36
normalized bonds :
 6-7 6-11 7-8 8-9 9-10 10-11 12-13 12-17 13-14 14-15 15-16 16-17 18-19 18-23
 19-20 20-21 21-22 22-23

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G1:OH,MeO,EtO,n-PrO,i-PrO,n-BuO,i-BuO,t-BuO,CO2H,NH2

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Match level :
1:Atom 2:Atom 3:Atom 4:Atom 5:Atom 6:Atom 7:Atom 8:Atom 9:Atom 10:Atom 11:Atom
12:Atom 13:Atom 14:Atom 15:Atom 16:Atom 17:Atom 18:Atom 19:Atom 20:Atom 21:Atom
22:Atom 23:Atom 24:Atom 26:Atom 29:Atom 30:Atom 31:Atom 32:Atom 33:Atom 34:Atom
35:Atom 36:Atom

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L Number	Hits	Search Text	DB	Time stamp
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FILE 'REGISTRY' ENTERED AT 18:09:29 ON 14 NOV 2004

L1 5 S HABI
L2 SCREEN 2067
L3 STRUCTURE UPLOADED
L4 QUE L3 AND L2
L5 136 S L4 FULL
L6 271118 S IMIDAZOLE
L7 117 S L5 AND L6
L8 163 S BIS IMIDAZOLE
L9 0 S L8 AND L5
L10 5 S HABI
L11 28 S BIS AND 2,4,5-TRIPHENYL AND IMIDAZOLE

FILE 'CAPLUS' ENTERED AT 18:36:12 ON 14 NOV 2004

L12 0 S 118-32-5/RN

FILE 'REGISTRY' ENTERED AT 18:36:39 ON 14 NOV 2004

FILE 'CAPLUS' ENTERED AT 18:36:39 ON 14 NOV 2004

L13 107 S L11
L14 0 S 118-32-5/RN
L15 73 S 811-32-5/RN
L16 38114 S PHOTORESIST OR RESIST COMPOSITION
L17 7 S L15 AND L16
L18 1 S PHOTOINITIATOR (P) HYDROPHILIC CARRIER

=>

L17 ANSWER 1 OF 7 CAPLUS COPYRIGHT 2004 ACS on STN

AN 2001:814256 CAPLUS

DN 135:364511

TI Dry film photoresists with uniform thickness and their photosensitive compositions containing acrylate polymers

IN Yamamoto, Naotoshi; Sakomoto, Yasuyuki

PA Nichigo Morton K. K., Japan

SO Jpn. Kokai Tokkyo Koho, 9 pp.

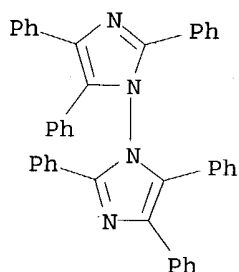
CODEN: JKXXAF

DT Patent

LA Japanese

FAN.CNT 1

	PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
PI	JP 2001312056	A2	20011109	JP 2000-128000	20000427
PRAI	JP 2000-128000		20000427		
AB	The compns., forming fine patterns with good etching resistance, comprise binders, monomers, photopolymn. initiators (preferably lophine dimer), and Et acrylate- and 2-ethylhexyl acrylate-polymerized polymers.				
IT	811-32-5, 2,4,5-Triphenylimidazole dimer				
RL	CAT (Catalyst use); USES (Uses)				
	(photopolymn. initiators; dry film photoresists with uniform thickness and smooth surfaces and their compns. containing sp. acrylate polymers)				
RN	811-32-5 CAPLUS				
CN	1,1'-Bi-1H-imidazole, 2,2',4,4',5,5'-hexaphenyl- (9CI) (CA INDEX NAME)				



L17 ANSWER 2 OF 7 CAPLUS COPYRIGHT 2004 ACS on STN

AN 1999:519007 CAPLUS

DN 131:177367

TI Patterning of **photoresist** layer containing base polymer, ethylenically unsaturated compound, and cleavage-type polymerization initiator

IN Takasaka, Eiji; Sato, Hiroaki

PA Nippon Synthetic Chemical Industry Co., Ltd., Japan

SO Jpn. Kokai Tokkyo Koho, 8 pp.

CODEN: JKXXAF

DT Patent

LA Japanese

FAN.CNT 1

	PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
PI	JP 11223944	A2	19990817	JP 1998-39763	19980204
PRAI	JP 1998-39763		19980204		
AB	Resist patterns are formed by imagewise exposing and developing of a photoresist layer on a metal substrate followed by exposure to active radiation. The photoresist composition contains a base polymer with 95-250 mg KOH/g acid value and 5000-200,000 weight average mol. weight, an ethylenically unsatd. compound containing ≥ 50 weight% ethylene				

oxide-modified trimethylolpropane triacrylate, and a cleavage-type polymerization initiator. The composition shows improved sensitivity and resolving power the resulting resist shows improved adhesion to the support, etching resistance, and metalizing resistance.

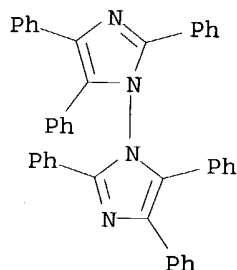
IT 811-32-5, 2,4,5-Triphenylimidazole dimer

RL: MOA (Modifier or additive use); USES (Uses)

(in patterning of **photoresist** containing cleavage-type polymerization initiator associated with active radiation exposure after development)

RN 811-32-5 CAPLUS

CN 1,1'-Bi-1H-imidazole, 2,2',4,4',5,5'-hexaphenyl- (9CI) (CA INDEX NAME)



L17 ANSWER 3 OF 7 CAPLUS COPYRIGHT 2004 ACS on STN

AN 1999:345926 CAPLUS

DN 131:52035

TI **Photoresist** film useful as etching resist and plating resist

IN Hyuga, Atsuyoshi; Sato, Hiroaki

PA Nippon Synthetic Chemical Industry Co., Ltd., Japan

SO Jpn. Kokai Tokkyo Koho, 9 pp.

CODEN: JKXXAF

DT Patent

LA Japanese

FAN.CNT 1

	PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
PI	JP 11149158	A2	19990602	JP 1997-330904	19971114
PRAI	JP 1997-330904		19971114		

AB The title **photoresist** film comprises a film support with thickness 10-30 μm and surface roughness (Ra) 0.001-0.015 μm on which (1) a photosensitive resin composition layer containing (a) a base polymer with acid value 95-250 mg KOH/g and weight average mol. weight 5000-200,000, (b) ethylenic unsatd. compds. including ≥ 50 weight% ethylene oxide-modified trimethylolpropane triacrylate, and (c) a self-cleavage-type initiator and (2) a protective film are laminated successively. The **photoresist** film shows high photosensitivity and provides a high resolution resist pattern with good peeling properties, adhesion to substrate, etch resistance, and plating properties.

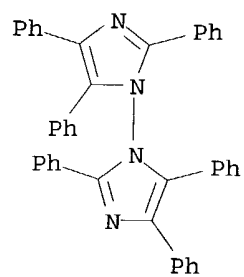
IT 811-32-5, 2,4,5-Triphenylimidazole dimer

RL: MOA (Modifier or additive use); TEM (Technical or engineered material use); USES (Uses)

(**photoresist** film comprising thickness and surface roughness-controlled support and photosensitive layer)

RN 811-32-5 CAPLUS

CN 1,1'-Bi-1H-imidazole, 2,2',4,4',5,5'-hexaphenyl- (9CI) (CA INDEX NAME)



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